

# MCP6401/1R/1U/2/4/6/7/9

## 1 MHz, 45 µA Op Amps

#### Features

- Low Quiescent Current: 45 μA (typical)
- Gain Bandwidth Product: 1 MHz (typical)
- · Rail-to-Rail Input and Output
- Supply Voltage Range: 1.8V to 6.0V
- Unity Gain Stable
- Extended Temperature Ranges:
- -40 ℃ to +125 ℃ (E temp)
- -40 °C to +150 °C (H temp)
- No Phase Reversal

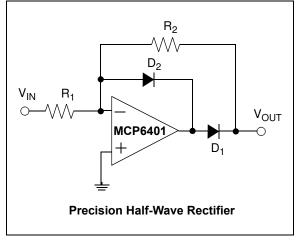
#### Applications

- · Portable Equipment
- · Battery Powered System
- Medical Instrumentation
- Automotive Electronics
- · Data Acquisition Equipment
- Sensor Conditioning
- Analog Active Filters

#### **Design Aids**

- SPICE Macro Models
- FilterLab<sup>®</sup> Software
- Microchip Advanced Part Selector (MAPS)
- Analog Demonstration and Evaluation Boards
- Application Notes

#### **Typical Application**

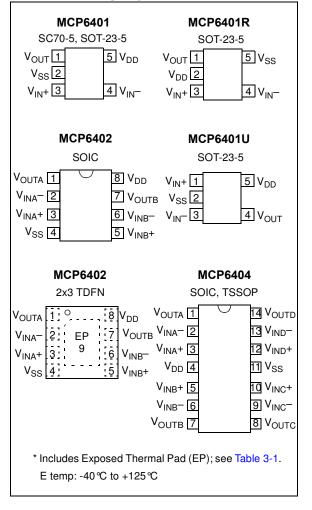


#### Description

The Microchip Technology Inc. MCP6401/1R/1U/2/4/6/7/9 family of operational amplifiers (op amps) has low quiescent current ( $45 \mu$ A, typical) and rail-to-rail input and output operation. This family is unity gain stable and has a gain bandwidth product of 1 MHz (typical). These devices operate with a power supply voltage of 1.8V to 6.0V. These features make the family of op amps well suited for single-supply, battery-powered applications.

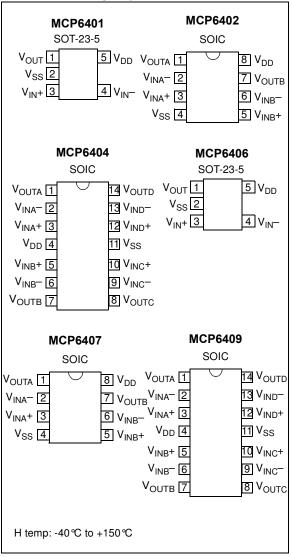
The MCP6401/1R/1U/2/4/6/7/9 family is designed with Microchip's advanced CMOS process and offered in single, dual and quad packages. The devices are available in two extended temperature ranges (E temp and H temp) with different package types, which makes them well-suited for automotive and industrial applications.

# MCP6401/1R/1U/2/4/6/7/9



#### E Temp Package Types

#### H Temp Package Types



#### 1.0 ELECTRICAL CHARACTERISTICS

#### 1.1 Absolute Maximum Ratings †

V <sub>DD</sub> – V <sub>SS</sub>
Current at Input Pins±2 mA
Analog Inputs (V_{IN+}, V_{IN-}) \dagger \dagger
All Other Inputs and Outputs $V_{SS}{-}0.3V$ to $V_{DD}{+}0.3V$
Difference Input Voltage $ V_{DD} - V_{SS} $
Output Short-Circuit CurrentContinuous
Current at Output and Supply Pins±30 mA
Storage Temperature65 °C to +150 °C
Maximum Junction Temperature (T <sub>J</sub> )+155°C
ESD Protection on All Pins (HBM; MM; CDM) $\ge$ 4 kV; 300V, 1500V

**†** Notice: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

**††** See Section 4.1.2 "Input Voltage Limits".

#### 1.2 MCP6401/1R/1U/2/4 Electrical Specifications

#### DC ELECTRICAL SPECIFICATIONS

**Electrical Characteristics**: Unless otherwise indicated,  $T_A = +25 \text{ °C}$ ,  $V_{DD} = +1.8 \text{ v}$  to +6.0 v,  $V_{SS} = \text{GND}$ ,  $V_{CM} = V_{DD}/2$ ,  $V_{OUT} \approx V_{DD}/2$ ,  $V_L = V_{DD}D/2$  and  $R_L = 100 \text{ k}\Omega$  to  $V_L$  (Refer to Figure 1-1).

Parameters	Sym	Min	Тур	Мах	Units	Temp	Parts (Note 1)	Conditions
Input Offset								
Input Offset Voltage	V <sub>OS</sub>	-4.5	±0.8	+4.5	mV		E, H	$V_{CM} = V_{SS}$
		—	±1.0	-	mV	+125℃	E	
		—	±1.5		mV	+150°C	Н	
Input Offset Drift with Temperature	$\Delta V_{OS} / \Delta T_A$	_	±2.0	_	µV/℃	-40 ℃ to +125 ℃	E	$V_{CM} = V_{SS}$
		_	±2.5	_	µV/℃	-40 ℃ to +150 ℃	Н	
Power Supply	PSRR	63	78	_	dB		E, H	$V_{CM} = V_{SS}$
Rejection Ratio		—	75	-	dB	+125℃	E	
		—	73		dB	+150°C	Н	
Input Bias Current ar	nd Impedan	се						
Input Bias Current	Ι <sub>Β</sub>	_	1	100	pА		E, H	
		_	30	_	pА	+85 <i>°</i> C	Е, Н	
			800		pА	+125℃	E	
		—	7		nA	+150℃	Н	
Input Offset Current	I <sub>OS</sub>	_	1		pА		E, H	
		_	5		pА	+85℃	E, H	
		—	20	—	pА	+125℃	E	
			45	_	pА	+150℃	Н	

Note 1: E part stands for the one whose operating temperature range is from -40 ℃ to +125 ℃ and H part stands for the one whose operating temperature range is from -40 ℃ to +150 ℃.

2: Figure 2-14 shows how V<sub>CMR</sub> changes across temperature.

#### DC ELECTRICAL SPECIFICATIONS (CONTINUED)

 $\label{eq:trical characteristics: Unless otherwise indicated, $T_A = +25 °C, V_{DD} = +1.8$ v to +6.0$ v, $V_{SS} = GND$, $V_{CM} = V_{DD}/2$, $V_{OUT} \approx V_{DD}/2$, $V_L = V_{DD}D/2$ and $R_L = 100 $k\Omega$ to $V_L$ (Refer to Figure 1-1)$.}$ 

$V_{CM} = V_{DD}/2, V_{OUT} \approx V_{OUT}$	<i>DD'</i> =, •L		<u></u>		(			
Parameters	Sym	Min	Тур	Max	Units	Temp	Parts (Note 1)	Conditions
Common Mode Input Impedance	Z <sub>CM</sub>	_	10 <sup>13</sup>   6	_	Ω  pF		E, H	
Differential Input Impedance	Z <sub>DIFF</sub>	—	10 <sup>13</sup>   6		Ω∥pF		E, H	
Common Mode								
Common Mode Input	V <sub>CMR</sub>	V <sub>SS</sub> -0.20	_	V <sub>DD</sub> +0.20	V		E, H	V <sub>DD</sub> = 1.8V
Voltage Range		V <sub>SS</sub> -0.05	_	V <sub>DD</sub> +0.05	V	+125℃	E	
(Note 2)		V <sub>SS</sub>	_	V <sub>DD</sub>	V	+150℃	Н	
		V <sub>SS</sub> -0.30	_	V <sub>DD</sub> +0.30	V		E, H	$V_{DD} = 6.0 V$
		V <sub>SS</sub> -0.15	_	V <sub>DD</sub> +0.15	V	+125℃	E	
		V <sub>SS</sub> -0.10	_	V <sub>DD</sub> +0.10	V	+150℃	Н	
Common Mode Rejection Ratio	CMRR	56	71	_	dB		E, H	$V_{CM} = -0.2V$ to 2.0V, $V_{DD} = 1.8V$
		_	68	—	dB	+125℃	E	V <sub>CM</sub> = -0.05V to 1.85V V <sub>DD</sub> = 1.8V
		—	65	—	dB	+150℃	Н	V <sub>CM</sub> = 0V to 1.8V, V <sub>DD</sub> = 1.8V
		63	78	—	dB		E, H	$V_{CM} = -0.3V$ to 6.3V, $V_{DD} = 6.0V$
		—	76	—	dB	+125℃	E	V <sub>CM</sub> = -0.15V to 6.15V V <sub>DD</sub> = 6.0V
			75	—	dB	+150℃	Н	$V_{CM} = -0.1V$ to 6.1V, $V_{DD} = 6.0V$
Open-Loop Gain							•	
DC Open-Loop Gain	A <sub>OL</sub>	90	110	_	dB		E, H	$V_{OUT} = 0.3V$ to $V_{DD}$ -
(Large Signal)	-	_	105	—	dB	+125℃	E	0.3V,
		_	100	_	dB	+150℃	Н	$V_{CM} = V_{SS}$
Output								
High-Level Output	V <sub>OH</sub>	1.790	1.792	_	V		E, H	V <sub>DD</sub> = 1.8V
Voltage	0.1		1.788	_	V	+125℃	E	$R_L = 10 \text{ k}\Omega$
			1.785	_	V	+150°C	Н	0.5V input overdrive
		5.980	5.985	_	V		E, H	V <sub>DD</sub> = 6.0V
		_	5.980	—	V	+125℃	E	$R_L = 10 \text{ k}\Omega$
		_	5.975	—	V	+150℃	Н	0.5V input overdrive
Low-Level Output	V <sub>OL</sub>		0.008	0.010	V		E, H	V <sub>DD</sub> = 1.8V
Voltage		—	0.012	—	V	+125℃	E	$R_L = 10 k\Omega$
		_	0.015	—	V	+150℃	Н	0.5V input overdrive
		_	0.015	0.020	V		E, H	V <sub>DD</sub> = 6.0V
		_	0.020	—	V	+125℃	E	$R_L = 10 k\Omega$
			0.025		V	+150°C	Н	0.5V input overdrive

**Note 1:** E part stands for the one whose operating temperature range is from -40 °C to +125 °C and H part stands for the one whose operating temperature range is from -40 °C to +150 °C.

**2:** Figure 2-14 shows how V<sub>CMR</sub> changes across temperature.

#### DC ELECTRICAL SPECIFICATIONS (CONTINUED)

			•		,					
<b>Electrical Characteristics</b> : Unless otherwise indicated, $T_A = +25 \text{ °C}$ , $V_{DD} = +1.8 \text{ v}$ to $+6.0 \text{ v}$ , $V_{SS} = \text{GND}$ , $V_{CM} = V_{DD}/2$ , $V_{OUT} \approx V_{DD}/2$ , $V_L = V_{DD}D/2$ and $R_L = 100 \text{ k}\Omega$ to $V_L$ (Refer to Figure 1-1).										
Parameters	Sym	Min	Тур	Мах	Units	Temp	Parts (Note 1)	Conditions		
Output Short-Circuit	I <sub>SC</sub>	_	±5	_	mA		E, H	V <sub>DD</sub> = 1.8V		
Current			±15		mA		E, H	$V_{DD} = 6.0V$		
Power Supply										
Supply Voltage	V <sub>DD</sub>	1.8		6.0	V		E, H			
Quiescent Current	۱ <sub>Q</sub>	20	45	70	μA		E, H	$I_{O} = 0, V_{DD} = 5.0V$		
per Amplifier		—	55	—	μA	+125℃	E	$V_{CM} = 0.2V_{DD}$		

**Note 1:** E part stands for the one whose operating temperature range is from -40 °C to +125 °C and H part stands for the one whose operating temperature range is from -40 °C to +150 °C.

μA

+150°C

Н

60

2: Figure 2-14 shows how V<sub>CMR</sub> changes across temperature.

#### AC ELECTRICAL SPECIFICATIONS

**Electrical Characteristics:** Unless otherwise indicated,  $T_A = +25$  °C,  $V_{DD} = +1.8$  to +6.0V,  $V_{SS} = GND$ ,  $V_{CM} = V_{DD}/2$ ,  $V_{OUT} \approx V_{DD}/2$ ,  $V_L = V_{DD}/2$ ,  $R_L = 100$  k $\Omega$  to  $V_L$  and  $C_L = 60$  pF (Refer to Figure 1-1).

Parameters	Sym	Min	Тур	Мах	Units	Parts	Conditions
AC Response							
Gain Bandwidth Product	GBWP	_	1	—	MHz	Е, Н	
Phase Margin	PM	_	65	—	0	Е, Н	G = +1 V/V
Slew Rate	SR	_	0.5	—	V/µs	Е, Н	
Noise							
Input Noise Voltage	E <sub>ni</sub>	_	3.6	_	μVp-р	E, H	f = 0.1 Hz to 10 Hz
Input Noise Voltage Density	e <sub>ni</sub>	_	28	_	nV/√Hz	Е, Н	f = 1 kHz
Input Noise Current Density	i <sub>ni</sub>		0.6	_	fA/√Hz	Е, Н	f = 1 kHz

#### **TEMPERATURE SPECIFICATIONS**

Electrical Characteristics: Unless ot	herwise ind	licated, V <sub>D</sub>	<sub>D</sub> = +1.8V	to +6.0V a	nd V <sub>SS</sub> =	GND.
Parameters	Sym	Min	Тур	Max	Units	Conditions
Temperature Ranges						
Operating Temperature Range	T <sub>A</sub>	-40	_	+125	°C	E temp parts (Note 1)
	T <sub>A</sub>	-40	—	+150	°C	H temp parts (Note 1)
Storage Temperature Range	T <sub>A</sub>	-65	—	+155	°C	
Thermal Package Resistances						
Thermal Resistance, 5L-SC70	$\theta_{JA}$	—	331	—	°C/W	
Thermal Resistance, 5L-SOT-23	$\theta_{JA}$	—	220.7	—	°C/W	
Thermal Resistance, 8L-SOIC	$\theta_{JA}$	—	149.5	—	°C/W	
Thermal Resistance, 8L-2x3 TDFN	$\theta_{JA}$	—	52.5	_	°C/W	
Thermal Resistance, 14L-SOIC	$\theta_{JA}$	—	95.3	—	°C/W	
Thermal Resistance, 14L-TSSOP	$\theta_{JA}$	_	100	—	°C/W	

**Note 1:** The internal junction temperature  $(T_J)$  must not exceed the absolute maximum specification of +155 °C.

#### 1.3 MCP6406/7/9 Electrical Specifications

#### DC ELECTRICAL SPECIFICATIONS

 $\label{eq:trical Characteristics: Unless otherwise indicated, $T_A = +25 °C, V_{DD} = +1.8V$ to +6.0V, $V_{SS} = GND$, $V_{CM} = V_{DD}/2$, $V_{OUT} ~ $V_{DD}/2$, $V_L = V_{DD}/2$ and $R_L = 100 $k\Omega$ to $V_L$ (Refer to Figure 1-1)$.}$ 

Parameters	Sym	Min	Тур	Мах	Units	Temp	Parts (Note 1)	Conditions
Input Offset								
Input Offset Voltage	V <sub>OS</sub>	-4.5		+4.5	mV		Е, Н	$V_{CM} = V_{SS}$
		-5.0	±1.0	+5.0	mV	+125℃	Е	
		-5.5	±1.5	+5.5	mV	+150 <i>°</i> C	Н	
Input Offset Drift with Temperature	$\Delta V_{OS}/DT_A$	_	±2.0	_	µV/℃	-40 ℃ to +125 ℃	E	V <sub>CM</sub> = V <sub>SS</sub>
		_	±2.5	_	µV/℃	-40 ℃ to +150 ℃	Н	
Power Supply	PSRR	63	78		dB		E, H	$V_{CM} = V_{SS}$
Rejection Ratio		60	75	_	dB	+125℃	E	
		58	73		dB	+150℃	Н	
Input Bias Current a	and Impedar	ice						
Input Bias Current	I <sub>B</sub>		±1	100	pА		E, H	
			30	_	pА	+85℃	Е, Н	
			800	2000	pА	+125℃	E	
		_	7	12	nA	+150 <i>°</i> C	Н	
Input Offset Current	I <sub>OS</sub>	_	1	_	pА		E, H	
			5	_	pА	+85 <i>°</i> C	E, H	
		_	20	_	pА	+125℃	E	
		_	45	_	pА	+150 <i>°</i> C	Н	
Common Mode Input Impedance	Z <sub>CM</sub>	_	10 <sup>13</sup>   6		Ω∥pF		E, H	
Differential Input Impedance	Z <sub>DIFF</sub>	—	10 <sup>13</sup>   6		Ω  pF		Е, Н	
Common Mode								
Common Mode	V <sub>CMR</sub>	V <sub>SS</sub> -0.20	—	V <sub>DD</sub> +0.20	V		Е, Н	$V_{DD} = 1.8V$
Input Voltage Range		V <sub>SS</sub> -0.05	—	V <sub>DD</sub> +0.05	V	+125℃	E	
(Note 2)		$V_{SS}$		V <sub>DD</sub>	V	+150 <i>°</i> C	Н	
		V <sub>SS</sub> -0.30		V <sub>DD</sub> +0.30	V		Е, Н	$V_{DD} = 6.0V$
		V <sub>SS</sub> -0.15		V <sub>DD</sub> +0.15	V	+125℃	E	]
		V <sub>SS</sub> -0.10	_	V <sub>DD</sub> +0.10	V	+150 <i>°</i> C	Н	

Note 1: E part stands for the one whose operating temperature range is from -40 ℃ to +125 ℃ and H part stands for the one whose operating temperature range is from -40 ℃ to +150 ℃.

2: Figure 2-14 shows how V<sub>CMR</sub> changes across temperature.

#### DC ELECTRICAL SPECIFICATIONS (CONTINUED)

Electrical Character $V_{CM} = V_{DD}/2, V_{OUT} $ »								/ <sub>SS</sub> = GND,
Parameters	Sym	Min	Тур	Мах	Units	Temp	Parts (Note 1)	Conditions
Common Mode Rejection Ratio	CMRR	56	71	_	dB		E, H	$V_{CM}$ = -0.2V to 2.0V, $V_{DD}$ = 1.8V
		53	68	_	dB	+125℃	E	$V_{CM} = -0.05V$ to 1.85V, $V_{DD} = 1.8V$
		50	65		dB	+150℃	Н	$V_{CM} = 0V$ to 1.8V, $V_{DD} = 1.8V$
		63	78		dB		E, H	$V_{CM}$ = -0.3V to 6.3V, $V_{DD}$ = 6.0V
		61	76		dB	+125 <i>°</i> C	E	$V_{CM} = -0.15V$ to 6.15V, $V_{DD} = 6.0V$
		60	75		dB	+150 <i>°</i> C	Н	$V_{CM} = -0.1V$ to 6.1V, $V_{DD} = 6.0V$
Open-Loop Gain								
DC Open-Loop Gain	A <sub>OL</sub>	90	110		dB		Е, Н	$V_{OUT} = 0.3V$ to
(Large Signal)		88	105		dB	+125℃	Е	$V_{DD}$ -0.3V, $V_{CM} = V_{SS}$
		85	100		dB	+150 <i>°</i> C	Н	
Output								
High-Level Output	V <sub>OH</sub>	1.790	1.792	—	V		E, H	$V_{DD} = 1.8V$
Voltage		1.785	1.788		V	+125℃	E	$R_L = 10 k\Omega$
		1.782	1.785	_	V	+150 <i>°</i> C	Н	0.5V input overdrive
		5.980	5.985	—	V		E, H	$V_{DD} = 6.0 V$
		5.970	5.980		V	+125℃	Е	$R_L = 10 \text{ k}\Omega$ 0.5V input overdrive
		5.965	5.975		V	+150 <i>°</i> C	Н	
Low-Level Output	V <sub>OL</sub>	—	0.008	0.010	V		Е, Н	V <sub>DD</sub> = 1.8V
Voltage			0.012	0.015	V	+125℃	Е	$R_L = 10 k\Omega$
		—	0.015	0.018	V	+150 <i>°</i> C	Н	0.5V input overdrive
		—	0.015	0.020	V		E, H	$V_{DD} = 6.0 V$
		_	0.020	0.030	V	+125℃	E	$R_L = 10 k\Omega$
		—	0.025	0.035	V	+150 <i>°</i> C	Н	0.5V input overdrive
Output Short-Circuit	I <sub>SC</sub>	—	±5	—	mA		E, H	$V_{DD} = 1.8V$
Current		—	±15		mA		Е, Н	$V_{DD} = 6.0 V$
Power Supply								
Supply Voltage	V <sub>DD</sub>	1.8		6.0	V		E, H	
Quiescent Current	l <sub>Q</sub>	20	45	70	μA		Е, Н	$I_{O} = 0, V_{DD} = 5.0V$
per Amplifier	3	30	55	80	μA	+125℃	E	$V_{CM} = 0.2V_{DD}$
		35	60	90	μA	+150 <i>°</i> C	Н	1

**Note 1:** E part stands for the one whose operating temperature range is from -40 °C to +125 °C and H part stands for the one whose operating temperature range is from -40 °C to +150 °C.

2: Figure 2-14 shows how V<sub>CMR</sub> changes across temperature.

#### AC ELECTRICAL SPECIFICATIONS

Parameters	Sym	Min	Тур	Мах	Units	Part	Conditions			
AC Response										
Gain Bandwidth Product	GBWP	_	1		MHz	Е, Н				
Phase Margin	PM		65		0	Е, Н	G = +1 V/V			
Slew Rate	SR		0.5		V/µs	Е, Н				
Noise							_			
Input Noise Voltage	E <sub>ni</sub>		3.6		μVр-р	E, H	f = 0.1 Hz to 10 Hz			
Input Noise Voltage Density	e <sub>ni</sub>		28		nV/√Hz	Е, Н	f = 1 kHz			
Input Noise Current Density	i <sub>ni</sub>	_	0.6	_	fA/√Hz	E, H	f = 1 kHz			

#### **TEMPERATURE SPECIFICATIONS**

Electrical Characteristics: Unless of	otherwise ind	icated, V <sub>DI</sub>	<sub>D</sub> = +1.8V	to +6.0V ai	nd $V_{SS} = 0$	GND.				
Parameters	Sym	Min	Тур	Max	Units	Conditions				
Temperature Ranges										
Operating Temperature Range	T <sub>A</sub>	-40	—	+125	°C	E temp parts (Note 1)				
	T <sub>A</sub>	-40	—	+150	°C	H temp parts (Note 1)				
Storage Temperature Range	T <sub>A</sub>	-65		+155	°C					
Thermal Package Resistances										
Thermal Resistance, 5L-SOT-23	$\theta_{JA}$	_	220.7	—	°C/W					
Thermal Resistance, 8L-SOIC	$\theta_{JA}$	_	149.5	—	°C/W					
Thermal Resistance, 14L-SOIC	$\theta_{JA}$	_	95.3	—	°C/W					
	· ( <b>T</b> )		1.1							

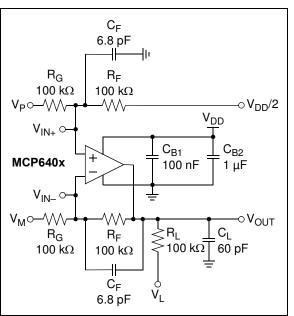
Note 1: The internal junction temperature ( $T_J$ ) must not exceed the absolute maximum specification of +155 °C.

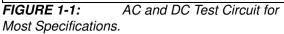
#### 1.4 Test Circuits

The circuit used for most DC and AC tests is shown in Figure 1-1. This circuit can independently set V<sub>CM</sub> and V<sub>OUT</sub>; see Equation 1-1. Note that V<sub>CM</sub> is not the circuit's Common Mode voltage ( $(V_P + V_M)/2$ ), and that V<sub>OST</sub> includes V<sub>OS</sub> plus the effects (on the input offset error, V<sub>OST</sub>) of temperature, CMRR, PSRR and A<sub>OL</sub>.

#### **EQUATION 1-1:**

$\begin{split} G_{DM} &= R_F / R_G \\ V_{CM} &= (V_P + V_{DD} / 2) / 2 \\ V_{OST} &= V_{IN-} - V_{IN+} \\ V_{OUT} &= (V_{DD} / 2) + (V_P - V_M) + V_{OST} (1 + G) \end{split}$	DM)
Where:	
$G_{DM}$ = Differential Mode Gain	(V/V)
V <sub>CM</sub> = Op Amp's Common Mode Input Voltage	(V)
V <sub>OST</sub> = Op Amp's Total Input Offset Voltage	(mV)

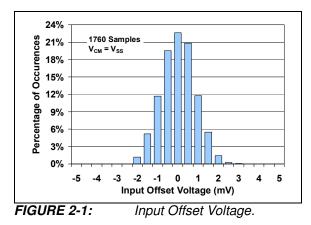


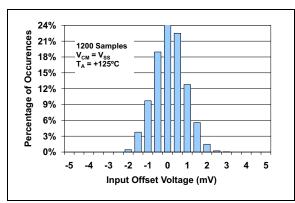


#### 2.0 TYPICAL PERFORMANCE CURVES

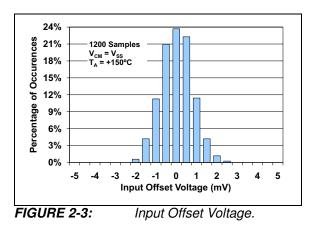
**Note:** The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore outside the warranted range.

**Note:** Unless otherwise indicated,  $T_A = +25$  °C,  $V_{DD} = +1.8V$  to +6.0V,  $V_{SS} = GND$ ,  $V_{CM} = V_{DD}/2$ ,  $V_{OUT} \approx V_{DD}/2$ ,  $V_L = V_{DD}/2$ ,  $R_L = 100 \text{ k}\Omega$  to  $V_L$  and  $C_L = 60 \text{ pF}$ .









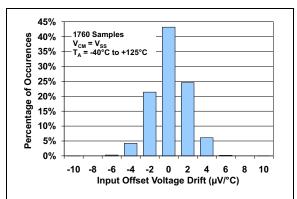


FIGURE 2-4:

Input Offset Voltage Drift.

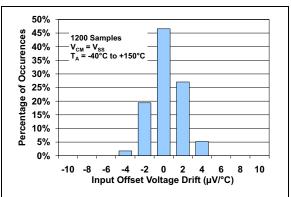
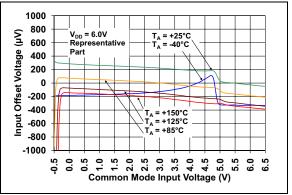


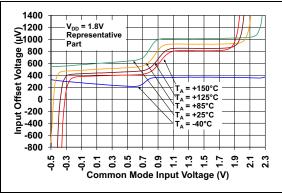
FIGURE 2-5: Input Offset Voltage Drift.



**FIGURE 2-6:** Input Offset Voltage vs. Common Mode Input Voltage with  $V_{DD} = 6.0V$ .

# MCP6401/1R/1U/2/4/6/7/9

**Note:** Unless otherwise indicated,  $T_A = +25$  °C,  $V_{DD} = +1.8V$  to +6.0V,  $V_{SS} = GND$ ,  $V_{CM} = V_{DD}/2$ ,  $V_{OUT} \approx V_{DD}/2$ ,  $V_L = V_{DD}/2$ ,  $R_L = 100 \text{ k}\Omega$  to  $V_L$  and  $C_L = 60 \text{ pF}$ .



**FIGURE 2-7:** Input Offset Voltage vs. Common Mode Input Voltage with  $V_{DD} = 1.8V$ .

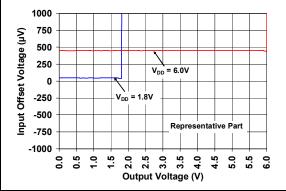


FIGURE 2-8: Input Offset Voltage vs. Output Voltage.

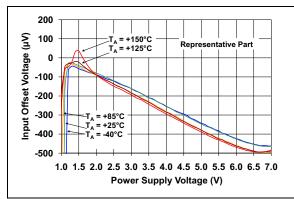


FIGURE 2-9: Input Offset Voltage vs. Power Supply Voltage.

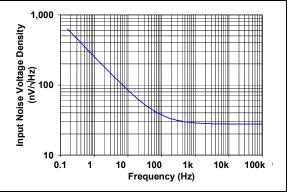


FIGURE 2-10: Input Noise Voltage Density vs. Frequency.

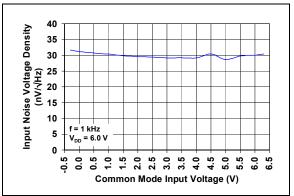


FIGURE 2-11: Input Noise Voltage Density vs. Common Mode Input Voltage.

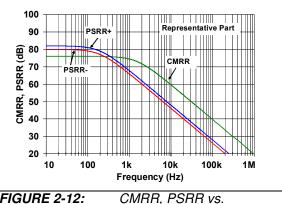
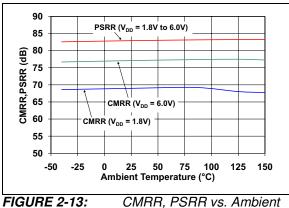


FIGURE 2-12: Cl Frequency.

**Note:** Unless otherwise indicated,  $T_A = +25 \text{ °C}$ ,  $V_{DD} = +1.8V$  to +6.0V,  $V_{SS} = GND$ ,  $V_{CM} = V_{DD}/2$ ,  $V_{OUT} \approx V_{DD}/2$ ,  $V_L = V_{DD}/2$ ,  $R_L = 100 \text{ k}\Omega$  to  $V_L$  and  $C_L = 60 \text{ pF}$ .



Temperature.

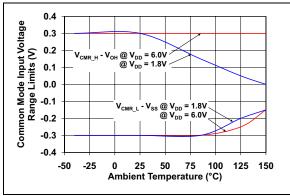
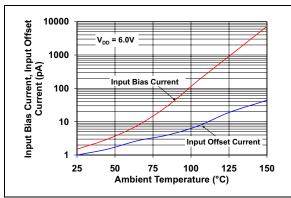


FIGURE 2-14: Common Mode Input Voltage Range Limits vs. Ambient Temperature.



**FIGURE 2-15:** Input Bias, Offset Current vs. Ambient Temperature.

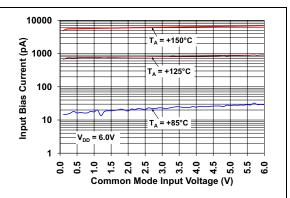
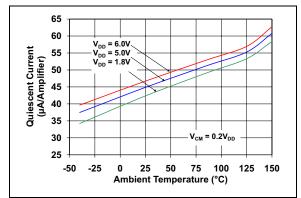


FIGURE 2-16: Input Bias Current vs. Common Mode Input Voltage.



**FIGURE 2-17:** Quiescent Current vs. Ambient Temperature.

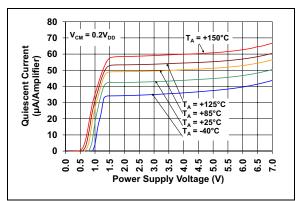


FIGURE 2-18: Quiescent Current vs. Power Supply Voltage.

# MCP6401/1R/1U/2/4/6/7/9

**Note:** Unless otherwise indicated,  $T_A = +25 \text{ °C}$ ,  $V_{DD} = +1.8V$  to +6.0V,  $V_{SS} = GND$ ,  $V_{CM} = V_{DD}/2$ ,  $V_{OUT} \approx V_{DD}/2$ ,  $V_L = V_{DD}/2$ ,  $R_L = 100 \text{ k}\Omega$  to  $V_L$  and  $C_L = 60 \text{ pF}$ .

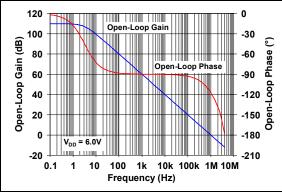
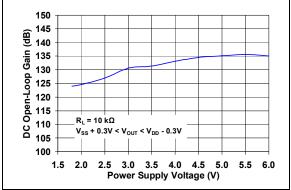


FIGURE 2-19: Open-Loop Gain, Phase vs. Frequency.



**FIGURE 2-20:** DC Open-Loop Gain vs. Power Supply Voltage.

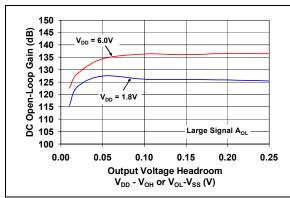
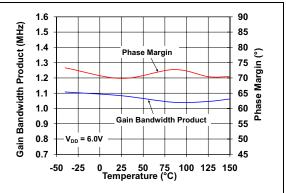


FIGURE 2-21: DC Open-Loop Gain vs. Output Voltage Headroom.



**FIGURE 2-22:** Gain Bandwidth Product, Phase Margin vs. Ambient Temperature.

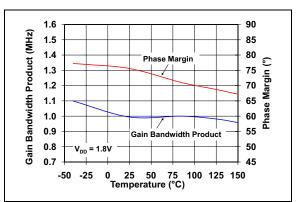


FIGURE 2-23: Gain Bandwidth Product, Phase Margin vs. Ambient Temperature.

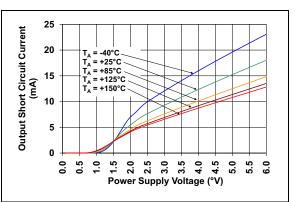


FIGURE 2-24: Output Short Circuit Current vs. Power Supply Voltage.

Note: Unless otherwise indicated,  $T_A = +25$  °C,  $V_{DD} = +1.8V$  to +6.0V,  $V_{SS} = GND$ ,  $V_{CM} = V_{DD}/2$ ,  $V_{OUT} \approx V_{DD}/2$ ,  $V_L = V_{DD}/2$ ,  $R_L = 100 \text{ k}\Omega$  to  $V_L$  and  $C_L = 60 \text{ pF}$ .

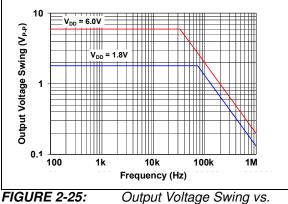


FIGURE 2-25: Frequency.

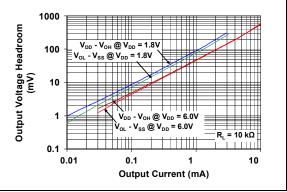
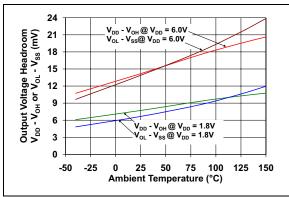
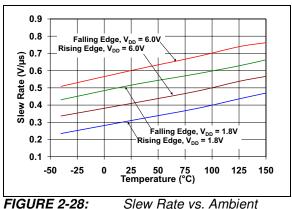


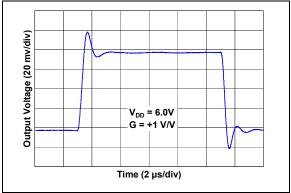
FIGURE 2-26: Output Voltage Headroom vs. Output Current.



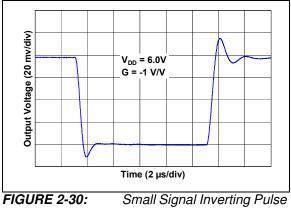
**FIGURE 2-27:** Output Voltage Headroom vs. Ambient Temperature.



Temperature.



**FIGURE 2-29:** Small Signal Non-Inverting Pulse Response.



Response.

# MCP6401/1R/1U/2/4/6/7/9

**Note:** Unless otherwise indicated,  $T_A = +25 \text{ °C}$ ,  $V_{DD} = +1.8V$  to +6.0V,  $V_{SS} = GND$ ,  $V_{CM} = V_{DD}/2$ ,  $V_{OUT} \approx V_{DD}/2$ ,  $V_L = V_{DD}/2$ ,  $R_L = 100 \text{ k}\Omega$  to  $V_L$  and  $C_L = 60 \text{ pF}$ .

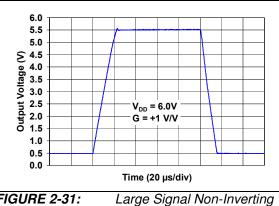


FIGURE 2-31: Pulse Response.

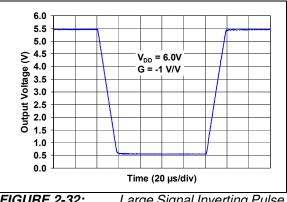
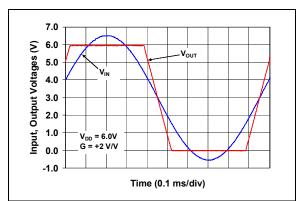


FIGURE 2-32: Large Signal Inverting Pulse Response.



*FIGURE 2-33:* The *MCP6401/1R/1U/2/4/6/7/9 Shows No Phase Reversal.* 

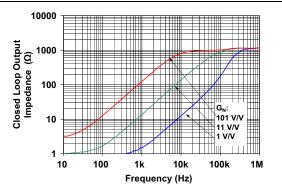
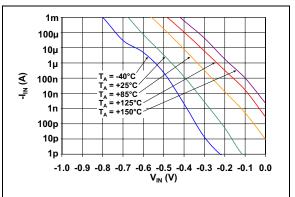


FIGURE 2-34: Closed Loop Output Impedance vs. Frequency.



**FIGURE 2-35:** Measured Input Current vs. Input Voltage (below V<sub>SS</sub>).

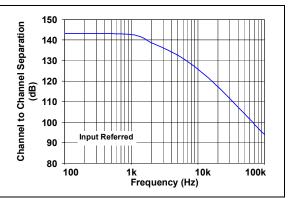


FIGURE 2-36: Channel-to-Channel Separation vs. Frequency (MCP6402/4/7/9 only).

#### 3.0 PIN DESCRIPTIONS

Descriptions of the pins are listed in Table 3-1.

#### TABLE 3-1:PIN FUNCTION TABLE 1

MCP6401	MCP6401R	MCP6401U	MCP	6402	MCP6404	MCP6406	MCP6407	MCP6409		
SC70-5, SOT-23-5	SOT-23-5	SOT-23-5	SOIC	2x3 TDFN	SOIC, TSSOP	SOT-23-5	SOIC	SOIC	Symbol	Description
1	1	4	1	1	1	1	1	1	V <sub>OUT</sub> , V <sub>OUTA</sub>	Analog Output (op amp A)
4	4	3	2	2	2	4	2	2	V <sub>IN</sub> -, V <sub>INA</sub> -	Inverting Input (op amp A)
3	3	1	3	3	3	3	3	3	V <sub>IN</sub> +, V <sub>INA</sub> +	Non-inverting Input (op amp A)
5	2	5	8	8	4	5	8	4	V <sub>DD</sub>	Positive Power Supply
—	_		5	5	5		5	5	V <sub>INB</sub> +	Non-inverting Input (op amp B)
—	_	_	6	6	6		6	6	V <sub>INB</sub> –	Inverting Input (op amp B)
—	—	_	7	7	7	-	7	7	V <sub>OUTB</sub>	Analog Output (op amp B)
—	—				8		—	8	V <sub>OUTC</sub>	Analog Output (op amp C)
—					9		_	9	V <sub>INC</sub> -	Inverting Input (op amp C)
—					10		_	10	V <sub>INC</sub> +	Non-inverting Input (op amp C)
2	5	2	4	4	11	2	4	11	V <sub>SS</sub>	Negative Power Supply
—	_	_		_	12	-	—	12	V <sub>IND</sub> +	Non-inverting Input (op amp D)
—	_				13		—	13	V <sub>IND</sub> -	Inverting Input (op amp D)
_	_	_		_	14	_	_	14	V <sub>OUTD</sub>	Analog Output (op amp D)
			_	9	_		_		EP	Exposed Thermal Pad (EP); must be connected to $V_{SS}$ .

#### 3.1 Analog Output (V<sub>OUT</sub>)

The output pin is low-impedance voltage source.

#### 3.2 Analog Inputs (V<sub>IN</sub>+, V<sub>IN</sub>-)

The non-inverting and inverting inputs are high-impedance CMOS inputs with low bias currents.

#### 3.3 Power Supply Pin (V<sub>DD</sub>, V<sub>SS</sub>)

The positive power supply (V<sub>DD</sub>) is 1.8V to 6.0V higher than the negative power supply (V<sub>SS</sub>). For normal operation, the other pins are at voltages between V<sub>SS</sub> and V<sub>DD</sub>.

Typically, these parts are used in a single (positive) supply configuration. In this case,  $V_{SS}$  is connected to ground and  $V_{DD}$  is connected to the supply.  $V_{DD}$  will need bypass capacitors.

#### 4.0 APPLICATION INFORMATION

The MCP6401/1R/1U/2/4/6/7/9 family of op amps is manufactured using Microchip's state-of-the-art CMOS process and is specifically designed for low-power, high-precision applications.

#### 4.1 Rail-to-Rail Input

#### 4.1.1 PHASE REVERSAL

The MCP6401/1R/1U/2/4/6/7/9 op amps are designed to prevent phase reversal when the input pins exceed the supply voltages. Figure 2-33 shows the input voltage exceeding the supply voltage with no phase reversal.

#### 4.1.2 INPUT VOLTAGE LIMITS

In order to prevent damage and/or improper operation of these amplifiers, the circuit must limit the voltages at the input pins (see Section 1.1 "Absolute Maximum Ratings †").

The ESD protection on the inputs can be depicted as shown in Figure 4-1. This structure was chosen to protect the input transistors against many (but not all) over-voltage conditions, and to minimize the input bias current ( $I_B$ ).

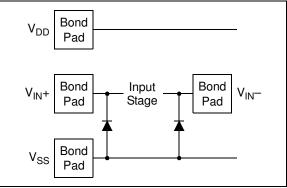


FIGURE 4-1: Simplified Analog Input ESD Structures.

The input ESD diodes clamp the inputs when they try to go more than one diode drop below  $V_{SS}$ . They also clamp any voltages that go well above  $V_{DD}$ ; their breakdown voltage is high enough to allow normal operation, but not low enough to protect against slow over-voltage (beyond  $V_{DD}$ ) events. Very fast ESD events (that meet the spec) are limited so that damage does not occur.

In some applications, it may be necessary to prevent excessive voltages from reaching the op amp inputs; Figure 4-2 shows one approach to protecting these inputs.

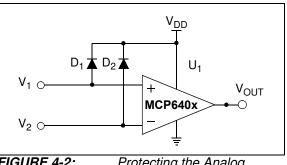


FIGURE 4-2: Protecting the Analog Inputs.

A significant amount of current can flow out of the inputs when the Common Mode voltage (V<sub>CM</sub>) is below ground (V<sub>SS</sub>); See Figure 2-35.

4.1.3 INPUT CURRENT LIMITS

In order to prevent damage and/or improper operation of these amplifiers, the circuit must limit the currents into the input pins (see Section 1.1 "Absolute Maximum Ratings †").

Figure 4-3 shows one approach to protecting these inputs. The resistors  $R_1$  and  $R_2$  limit the possible currents in or out of the input pins (and the ESD diodes,  $D_1$  and  $D_2$ ). The diode currents will go through either  $V_{DD}$  or  $V_{SS}$ .

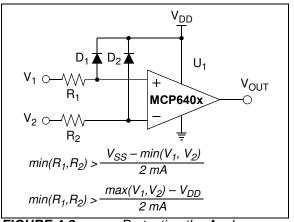


FIGURE 4-3: Protecting the Analog Inputs.

#### 4.1.4 NORMAL OPERATION

The input stage of the MCP6401/1R/1U/2/4/6/7/9 op amps use two differential input stages in parallel. One operates at a low Common Mode input voltage (V<sub>CM</sub>), while the other operates at a high V<sub>CM</sub>. With this topology, the device operates with a V<sub>CM</sub> up to 300 mV above V<sub>DD</sub> and 300 mV below V<sub>SS</sub> (see Figure 2-14). The input offset voltage is measured at V<sub>CM</sub> = V<sub>SS</sub> - 0.3V and V<sub>DD</sub> + 0.3V to ensure proper operation.

The transition between the input stages occurs when  $V_{CM}$  is near  $V_{DD}$  – 1.1V (see Figures 2-6 and 2-7). For the best distortion performance and gain linearity, with non-inverting gains, avoid this region of operation.

#### 4.2 Rail-to-Rail Output

The output voltage range of the MCP6401/1R/1U/2/4/6/7/9 op amps is V<sub>SS</sub> + 20 mV (minimum) and V<sub>DD</sub> - 20 mV (maximum) when R<sub>L</sub> = 10 k $\Omega$  is connected to V<sub>DD</sub>/2 and V<sub>DD</sub> = 6.0V. Refer to Figures 2-26 and 2-27 for more information.

#### 4.3 Capacitive Loads

Driving large capacitive loads can cause stability problems for voltage feedback op amps. As the load capacitance increases, the feedback loop's phase margin decreases and the closed-loop bandwidth is reduced. This produces gain peaking in the frequency response, with overshoot and ringing in the step response. While a unity-gain buffer (G = +1 V/V) is the most sensitive to capacitive loads, all gains show the same general behavior.

When driving large capacitive loads with these op amps (e.g., > 100 pF when G = +1 V/V), a small series resistor at the output ( $R_{ISO}$  in Figure 4-4) improves the feedback loop's phase margin (stability) by making the output load resistive at higher frequencies. The bandwidth will be generally lower than the bandwidth with no capacitance load.

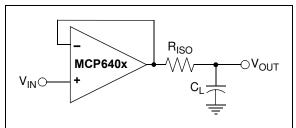
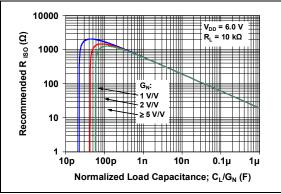


FIGURE 4-4: Output Resistor, R<sub>ISO</sub> Stabilizes Large Capacitive Loads.

Figure 4-5 gives recommended  $R_{ISO}$  values for different capacitive loads and gains. The x-axis is the normalized load capacitance ( $C_L/G_N$ ), where  $G_N$  is the circuit's noise gain. For non-inverting gains,  $G_N$  and the Signal Gain are equal. For inverting gains,  $G_N$  is 1+|Signal Gain| (e.g., -1 V/V gives  $G_N = +2$  V/V).



**FIGURE 4-5:** Recommended R<sub>ISO</sub> Values for Capacitive Loads.

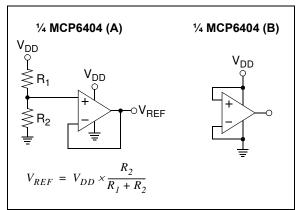
After selecting  $R_{ISO}$  for your circuit, double-check the resulting frequency response peaking and step response overshoot. Modify  $R_{ISO}$ 's value until the response is reasonable. Bench evaluation and simulations with the MCP6401/1R/1U/2/4/6/7/9 SPICE macro model are very helpful.

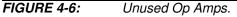
#### 4.4 Supply Bypass

With this family of operational amplifiers, the power supply pin ( $V_{DD}$  for single-supply) should have a local bypass capacitor (i.e., 0.01 µF to 0.1 µF) within 2 mm for good high frequency performance. It can use a bulk capacitor (i.e., 1 µF or larger) within 100 mm to provide large, slow currents. This bulk capacitor can be shared with other analog parts.

#### 4.5 Unused Op Amps

An unused op amp in quad packages (MCP6404 or MCP6409) should be configured as shown in Figure 4-6. These circuits prevent the output from toggling and causing crosstalk. Circuit A sets the op amp at its minimum noise gain. The resistor divider produces any desired reference voltage within the output voltage range of the op amp, which buffers that reference voltage. Circuit B uses the minimum number of components and operates as a comparator, but it may draw more current.

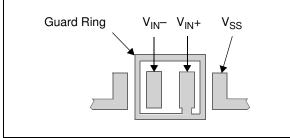




#### 4.6 PCB Surface Leakage

In applications where low input bias current is critical, Printed Circuit Board (PCB) surface leakage effects need to be considered. Surface leakage is caused by humidity, dust or other contamination on the board. Under low humidity conditions, a typical resistance between nearby traces is  $10^{12}\Omega$ . A 5V difference would cause 5 pA of current to flow; which is greater than the MCP6401/1R/1U/2/4/6/7/9 family's bias current at +25 °C (±1.0 pA, typical).

The easiest way to reduce surface leakage is to use a guard ring around sensitive pins (or traces). The guard ring is biased at the same voltage as the sensitive pin. An example of this type of layout is shown in Figure 4-7.



**FIGURE 4-7:** Example Guard Ring Layout for Inverting Gain.

- 1. Non-inverting Gain and Unity-Gain Buffer:
  - a) Connect the non-inverting pin (V<sub>IN</sub>+) to the input with a wire that does not touch the PCB surface.
  - b) Connect the guard ring to the inverting input pin (V<sub>IN</sub>-). This biases the guard ring to the Common Mode input voltage.
- 2. Inverting Gain and Transimpedance Gain Amplifiers (convert current to voltage, such as photo detectors):
  - a) Connect the guard ring to the non-inverting input pin (V<sub>IN</sub>+). This biases the guard ring to the same reference voltage as the op amp (e.g., V<sub>DD</sub>/2 or ground).
  - b) Connect the inverting pin (V\_{IN}-) to the input with a wire that does not touch the PCB surface.

#### 4.7 Application Circuits

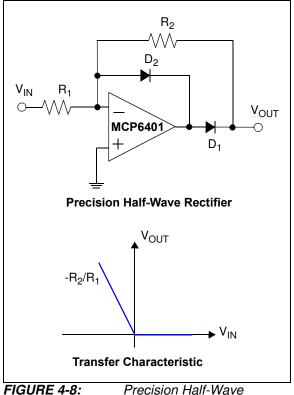
## 4.7.1 PRECISION HALF-WAVE RECTIFIER

The precision half-wave rectifier, which is also known as a super diode, is a configuration obtained with an operational amplifier in order to have a circuit behave like an ideal diode and rectifier. It effectively cancels the forward voltage drop of the diode so that very low level signals can still be rectified with minimal error. This can be useful for high-precision signal processing. The MCP6401/1R/1U/2/4/6/7/9 op amps have high input impedance, low input bias current and rail-to-rail input/output, which makes this device suitable for precision rectifier applications.

Figure 4-8 shows a precision half-wave rectifier and its transfer characteristic. The rectifier's input impedance is determined by the input resistor  $R_1$ . To avoid loading effect, it must be driven from a low-impedance source.

When  $V_{\text{IN}}$  is greater than zero,  $D_1$  is OFF,  $D_2$  is ON, and  $V_{\text{OUT}}$  is zero. When  $V_{\text{IN}}$  is less than zero,  $D_1$  is ON,  $D_2$  is OFF, and  $V_{\text{OUT}}$  is the  $V_{\text{IN}}$  with an amplification of  $-R_2/R_1$ .

The rectifier circuit shown in Figure 4-8 has the benefit that the op amp never goes in saturation, so the only thing affecting its frequency response is the amplification and the gain bandwidth product.



Rectifier.

Precision Half-Wave

#### 4.7.2 BATTERY CURRENT SENSING

The MCP6401/1R/1U/2/4/6/7/9 op amps' Common Mode Input Range, which goes 0.3V beyond both supply rails, supports their use in high-side and low-side battery current sensing applications. The low quiescent current (45  $\mu$ A, typical) helps prolong battery life, and the rail-to-rail output supports detection of low currents.

Figure 4-9 shows a high-side battery current sensor circuit. The 10 $\Omega$  resistor is sized to minimize power losses. The battery current (I<sub>DD</sub>) through the 10 $\Omega$  resistor causes its top terminal to be more negative than the bottom terminal. This keeps the Common Mode input voltage of the op amp below V<sub>DD</sub>, which is within its allowed range. The output of the op amp will also be below V<sub>DD</sub>, which is within its Maximum Output Voltage Swing specification.

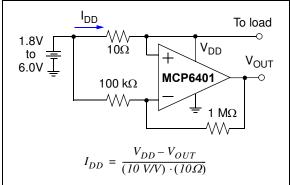


FIGURE 4-9: Supply Current Sensing.

#### 4.7.3 INSTRUMENTATION AMPLIFIER

The MCP6401/1R/1U/2/4/6/7/9 op amps are well suited for conditioning sensor signals in batterypowered applications. Figure 4-10 shows a two op amp instrumentation amplifier, using the MCP6402, that works well for applications requiring rejection of Common Mode noise at higher gains. The reference voltage ( $V_{REF}$ ) is supplied by a low impedance source. In single supply applications,  $V_{BEF}$  is typically  $V_{DD}/2$ .

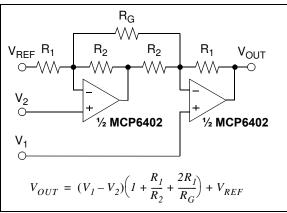


FIGURE 4-10: Two Op Amp Instrumentation Amplifier.

#### 5.0 DESIGN AIDS

Microchip provides the basic design tools needed for the MCP6401/1R/1U/2/4/6/7/9 family of op amps.

#### 5.1 SPICE Macro Model

The latest SPICE macro model for the MCP6401/1R/1U/2/4/6/7/9 op amp is available on the Microchip web site at www.microchip.com. The model was written and tested in official Orcad (Cadence) owned PSPICE. For other simulators, translation may be required.

The model covers a wide aspect of the op amp's electrical specifications. Not only does the model cover voltage, current, and resistance of the op amp, but it also covers the temperature and noise effects on the behavior of the op amp. The model has not been verified outside of the specification range listed in the op amp data sheet. The model behaviors under these conditions cannot be guaranteed to match the actual op amp performance.

Moreover, the model is intended to be an initial design tool. Bench testing is a very important part of any design and cannot be replaced with simulations. Also, simulation results using this macro model need to be validated by comparing them to the data sheet specifications and characteristic curves.

#### 5.2 FilterLab<sup>®</sup> Software

Microchip's FilterLab<sup>®</sup> software is an innovative software tool that simplifies analog active filter (using op amps) design. Available at no cost from the Microchip web site at www.microchip.com/filterlab, the FilterLab design tool provides full schematic diagrams of the filter circuit with component values. It also outputs the filter circuit in SPICE format, which can be used with the macro model to simulate actual filter performance.

#### 5.3 Microchip Advanced Part Selector (MAPS)

MAPS is a software tool that helps semiconductor professionals efficiently identify Microchip devices that fit a particular design requirement. Available at no cost from the Microchip website at www.microchip.com/maps, the MAPS is an overall selection tool for Microchip's product portfolio that includes Analog, Memory, MCUs and DSCs. Using this tool, you can define a filter to sort features for a parametric search of devices and export side-by-side technical comparison reports. Helpful links are also provided for Datasheets, Purchase, and Sampling of Microchip parts.

#### 5.4 Analog Demonstration and Evaluation Boards

Microchip offers a broad spectrum of Analog Demonstration and Evaluation Boards that are designed to help you achieve faster time to market. For a complete listing of these boards and their corresponding user's guides and technical information, visit www.microchip.com/analogtools, the Microchip web site.

Some boards that are especially useful are:

- MCP6XXX Amplifier Evaluation Board 1
- MCP6XXX Amplifier Evaluation Board 2
- MCP6XXX Amplifier Evaluation Board 3
- MCP6XXX Amplifier Evaluation Board 4
- Active Filter Demo Board Kit
- 5/6-Pin SOT-23 Evaluation Board, P/N VSUPEV2
- 8-Pin SOIC/MSOP/TSSOP/DIP Evaluation Board, P/N SOIC8EV
- 14-Pin SOIC/TSSOP/DIP Evaluation Board, P/N SOIC14EV

#### 5.5 Application Notes

The following Microchip Analog Design Note and Application Notes are available on the Microchip web site at www.microchip.com/appnotes and are recommended as supplemental reference resources.

- ADN003: "Select the Right Operational Amplifier for your Filtering Circuits", DS21821
- AN722: "Operational Amplifier Topologies and DC Specifications", DS00722
- AN723: "Operational Amplifier AC Specifications and Applications", DS00723
- AN884: "Driving Capacitive Loads With Op Amps", DS00884
- AN990: "Analog Sensor Conditioning Circuits An Overview", DS00990
- AN1177: "Op Amp Precision Design: DC Errors", DS01177
- AN1228: "Op Amp Precision Design: Random Noise", DS01228
- AN1297: "Microchip's Op Amp SPICE Macro Models", DS01297
- AN1332: "Current Sensing Circuit Concepts and Fundamentals", DS01332

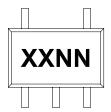
These application notes and others are listed in the design guide:

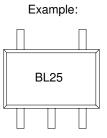
• "Signal Chain Design Guide", DS21825

#### 6.0 PACKAGING INFORMATION

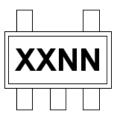
#### 6.1 Package Marking Information

5-Lead SC70 (MCP6401 only)





5-Lead SOT-23 (MCP6401/1R/1U, MCP6406)



Part Number	Code
MCP6401T-E/OT	NLNN
MCP6401T-H/OT	U8NN
MCP6401RT-E/OT	NMNN
MCP6401RT-H/OT	U9NN
MCP6401UT-E/OT	NPNN
MCP6401UT-H/OT	V8NN
MCP6406T-E/OT	ZXNN
MCP6406T-H/OT	ZYNN

# Example:

8-Lead TDFN (2 x 3)(MCP6402 only)



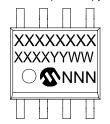
Part Number	Code
MCP6402T-E/MNY	AAW

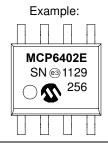


PIN 1

Example:

#### 8-Lead SOIC (150 mil)(MCP6401, MCP6402, MCP6407)

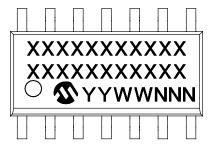




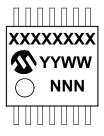
Legen	d: XXX Y YY WW NNN (e3) *	Customer-specific information Year code (last digit of calendar year) Year code (last 2 digits of calendar year) Week code (week of January 1 is week '01') Alphanumeric traceability code Pb-free JEDEC designator for Matte Tin (Sn) This package is Pb-free. The Pb-free JEDEC designator ((e3)) can be found on the outer packaging for this package.
Note:	be carrie	nt the full Microchip part number cannot be marked on one line, it will d over to the next line, thus limiting the number of available s for customer-specific information.

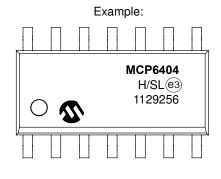
#### Package Marking Information (Continued)

14-Lead SOIC (150 mil) (MCP6404, MCP6409)



14-Lead TSSOP (MCP6404 only)





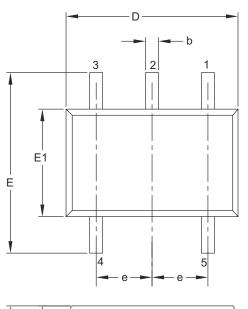
Example:

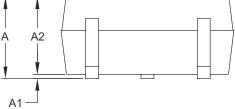


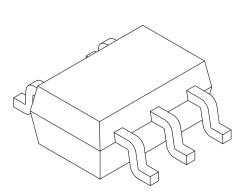
Legend	I: XXX Y YY WW NNN @3 *	Customer-specific information Year code (last digit of calendar year) Year code (last 2 digits of calendar year) Week code (week of January 1 is week '01') Alphanumeric traceability code Pb-free JEDEC designator for Matte Tin (Sn) This package is Pb-free. The Pb-free JEDEC designator ((e3)) can be found on the outer packaging for this package.
Note:	be carried	nt the full Microchip part number cannot be marked on one line, it will d over to the next line, thus limiting the number of available s for customer-specific information.

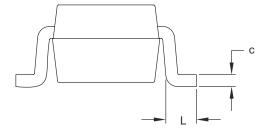
#### 5-Lead Plastic Small Outline Transistor (LT) [SC70]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging









	Units			6
Dimensio	Dimension Limits		NOM	MAX
Number of Pins	Ν		5	
Pitch	е		0.65 BSC	
Overall Height	А	0.80	-	1.10
Molded Package Thickness	A2	0.80	-	1.00
Standoff	A1	0.00	-	0.10
Overall Width	E	1.80	2.10	2.40
Molded Package Width	E1	1.15	1.25	1.35
Overall Length	D	1.80	2.00	2.25
Foot Length	L	0.10	0.20	0.46
Lead Thickness	С	0.08	_	0.26
Lead Width	b	0.15	—	0.40

#### Notes:

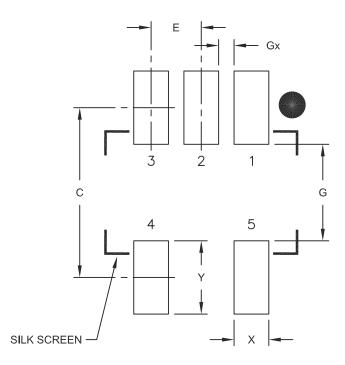
- 1. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.127 mm per side.
- 2. Dimensioning and tolerancing per ASME Y14.5M.

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-061B

#### 5-Lead Plastic Small Outline Transistor (LT) [SC70]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



#### RECOMMENDED LAND PATTERN

	Units		MILLIMETERS	
Dimensior	n Limits	MIN	NOM	MAX
Contact Pitch	E	0.65 BSC		
Contact Pad Spacing	С		2.20	
Contact Pad Width	Х			0.45
Contact Pad Length	Y			0.95
Distance Between Pads	G	1.25		
Distance Between Pads	Gx	0.20		

Notes:

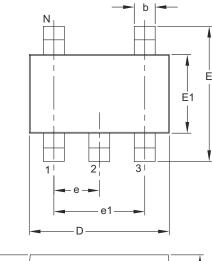
1. Dimensioning and tolerancing per ASME Y14.5M

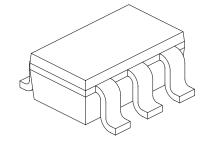
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

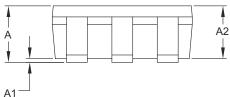
Microchip Technology Drawing No. C04-2061A

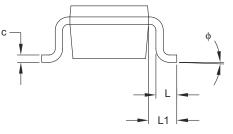
#### 5-Lead Plastic Small Outline Transistor (OT) [SOT-23]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging









	Units		MILLIMETERS	
Dimensio	Dimension Limits		MIN NOM	
Number of Pins	Ν		5	
Lead Pitch	е		0.95 BSC	
Outside Lead Pitch	e1		1.90 BSC	
Overall Height	Α	0.90	-	1.45
Molded Package Thickness	A2	0.89	-	1.30
Standoff	A1	0.00	-	0.15
Overall Width	E	2.20	-	3.20
Molded Package Width	E1	1.30	-	1.80
Overall Length	D	2.70	-	3.10
Foot Length	L	0.10	-	0.60
Footprint	L1	0.35	-	0.80
Foot Angle	¢	0°	-	30°
Lead Thickness	С	0.08	-	0.26
Lead Width	b	0.20	-	0.51

#### Notes:

1. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.127 mm per side.

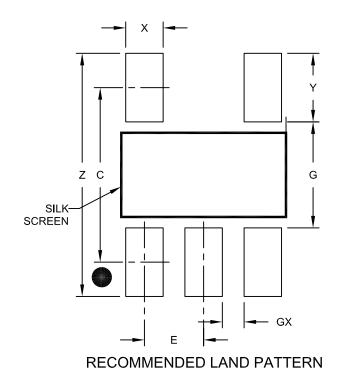
2. Dimensioning and tolerancing per ASME Y14.5M.

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-091B

#### 5-Lead Plastic Small Outline Transistor (OT) [SOT-23]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	Units		MILLIMETERS		
Dimensior	Dimension Limits		NOM	MAX	
Contact Pitch	E		0.95 BSC		
Contact Pad Spacing	С		2.80		
Contact Pad Width (X5)	X	0.6		0.60	
Contact Pad Length (X5)	Y	1.1		1.10	
Distance Between Pads	G	1.70			
Distance Between Pads	GX	0.35			
Overall Width	Z			3.90	

Notes:

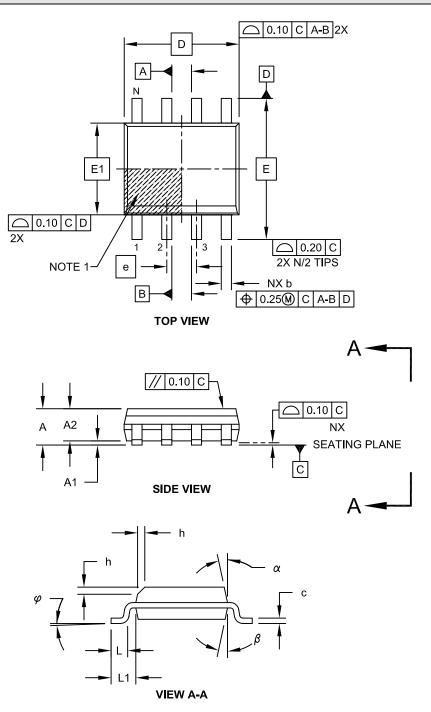
1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2091A

#### 8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm Body [SOIC]

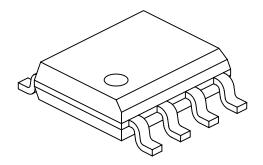
**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Microchip Technology Drawing No. C04-057C Sheet 1 of 2

#### 8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm Body [SOIC]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	MILLIMETERS			
Dimension Limits		MIN	NOM	MAX
Number of Pins	N		8	
Pitch	е		1.27 BSC	
Overall Height	Α	-	-	1.75
Molded Package Thickness	A2	1.25	-	-
Standoff §	A1	0.10	-	0.25
Overall Width	E	6.00 BSC		
Molded Package Width	E1	3.90 BSC		
Overall Length	D	4.90 BSC		
Chamfer (Optional)	h	0.25	-	0.50
Foot Length	L	0.40	-	1.27
Footprint	L1		1.04 REF	
Foot Angle	φ	0°	-	8°
Lead Thickness	c 0.17 - 0.2		0.25	
Lead Width	b	0.31	-	0.51
Mold Draft Angle Top	α	5°	-	15°
Mold Draft Angle Bottom	β	5°	-	15°

#### Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.

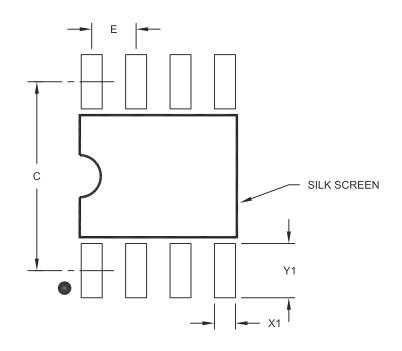
2. § Significant Characteristic

- 3. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15mm per side.
- 4. Dimensioning and tolerancing per ASME Y14.5M
  - BSC: Basic Dimension. Theoretically exact value shown without tolerances. REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing No. C04-057C Sheet 2 of 2

#### 8-Lead Plastic Small Outline (SN) – Narrow, 3.90 mm Body [SOIC]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN

Units		MILLIMETERS		
Dimension Limits		MIN	NOM	MAX
Contact Pitch	E		1.27 BSC	
Contact Pad Spacing	С		5.40	
Contact Pad Width (X8)	X1			0.60
Contact Pad Length (X8)	Y1			1.55

Notes:

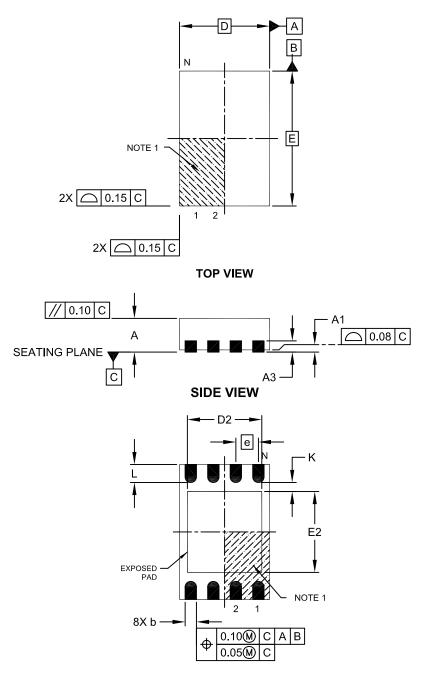
1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2057A

#### 8-Lead Plastic Dual Flat, No Lead Package (MN) – 2x3x0.75mm Body [TDFN]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging

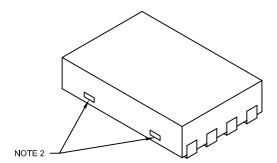


#### **BOTTOM VIEW**

Microchip Technology Drawing No. C04-129C Sheet 1 of 2

#### 8-Lead Plastic Dual Flat, No Lead Package (MN) – 2x3x0.75mm Body [TDFN]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	MILLIMETERS			
Dimension	Limits	MIN	NOM	MAX
Number of Pins	N		8	
Pitch	е		0.50 BSC	
Overall Height	A	0.70	0.75	0.80
Standoff	A1	0.00	0.02	0.05
Contact Thickness	A3	0.20 REF		
Overall Length	D	2.00 BSC		
Overall Width	E	3.00 BSC		
Exposed Pad Length	D2	1.20	-	1.60
Exposed Pad Width	E2	1.20	-	1.60
Contact Width	b	0.20	0.25	0.30
Contact Length	L	0.25	0.30	0.45
Contact-to-Exposed Pad	K	0.20	-	-

#### Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.

2. Package may have one or more exposed tie bars at ends.

3. Package is saw singulated

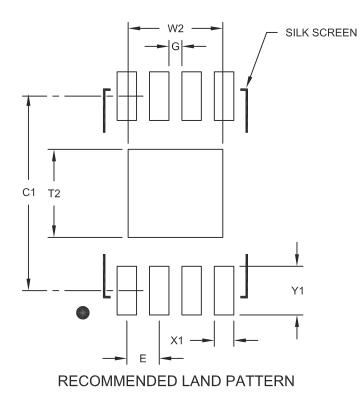
4. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances. REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing No. C04-129C

#### 8-Lead Plastic Dual Flat, No Lead Package (MN) – 2x3x0.75 mm Body [TDFN]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	L N		<u> </u>	
	Units		/ILLIMETER	3
Dimension	Dimension Limits		NOM	MAX
Contact Pitch	E	E 0.50 BSC		
Optional Center Pad Width	W2			1.46
Optional Center Pad Length	T2	1.3		1.36
Contact Pad Spacing	C1	3.00		
Contact Pad Width (X8)	X1			0.30
Contact Pad Length (X8)	Y1			0.75
Distance Between Pads	G	0.20		

Notes:

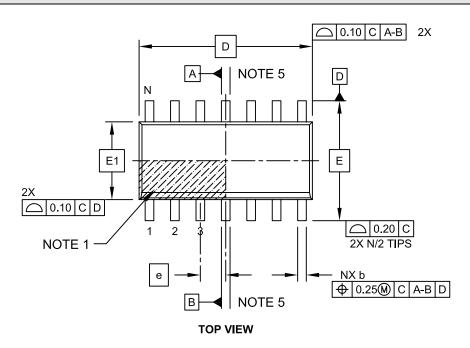
1. Dimensioning and tolerancing per ASME Y14.5M

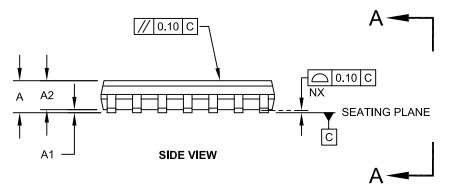
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

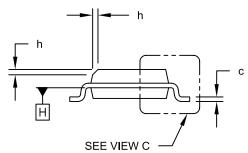
Microchip Technology Drawing No. C04-2129A

#### 14-Lead Plastic Small Outline (SL) - Narrow, 3.90 mm Body [SOIC]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging





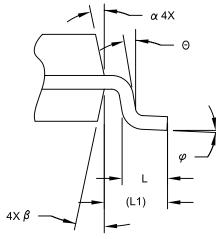


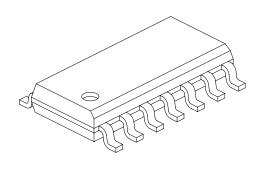


Microchip Technology Drawing No. C04-065C Sheet 1 of 2

#### 14-Lead Plastic Small Outline (SL) - Narrow, 3.90 mm Body [SOIC]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging





VIEW C

Units		MILLIMETERS			
Dimension Limits		MIN	NOM	MAX	
Number of Pins	N	14			
Pitch	е		1.27 BSC		
Overall Height	A	-	-	1.75	
Molded Package Thickness	A2	1.25			
Standoff §	A1	0.10 - 0.2			
Overall Width	E	6.00 BSC			
Molded Package Width	E1	3.90 BSC			
Overall Length	D	8.65 BSC			
Chamfer (Optional)	h	0.25 - 0.50			
Foot Length	L	0.40 1.2			
Footprint	L1	1.04 REF			
Lead Angle	Θ	0°	-	-	
Foot Angle	φ	0°	-	8°	
Lead Thickness	С	0.10	-	0.25	
Lead Width	b	0.31	-	0.51	
Mold Draft Angle Top	α	5° - 15°			
Mold Draft Angle Bottom	β	5°	-	15°	

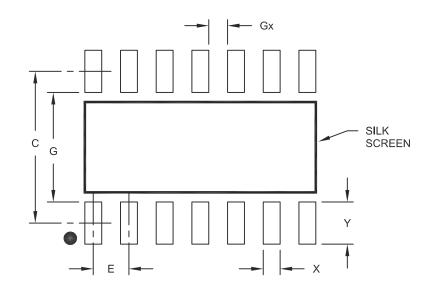
Notes:

- 1. Pin 1 visual index feature may vary, but must be located within the hatched area.
- 2. § Significant Characteristic
- Dimension D does not include mold flash, protrusions or gate burrs, which shall not exceed 0.15 mm per end. Dimension E1 does not include interlead flash or protrusion, which shall not exceed 0.25 mm per side.
- 4. Dimensioning and tolerancing per ASME Y14.5M BSC: Basic Dimension. Theoretically exact value shown without tolerances.
  - REF: Reference Dimension, usually without tolerance, for information purposes only.
- 5. Datums A & B to be determined at Datum H.

Microchip Technology Drawing No. C04-065C Sheet 2 of 2

14-Lead Plastic Small Outline (SL) - Narrow, 3.90 mm Body [SOIC]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



#### RECOMMENDED LAND PATTERN

	Units		MILLIMETERS			
Dimension	Dimension Limits		NOM	MAX		
Contact Pitch	E	1.27 BSC				
Contact Pad Spacing	С		5.40			
Contact Pad Width	Х			0.60		
Contact Pad Length	Y			1.50		
Distance Between Pads	Gx	0.67				
Distance Between Pads	G	3.90				

Notes:

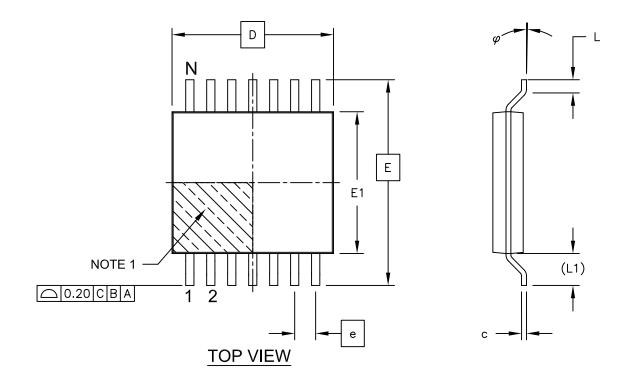
1. Dimensioning and tolerancing per ASME Y14.5M

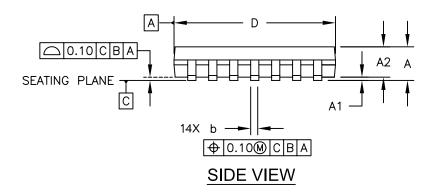
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2065A

#### 14-Lead Plastic Thin Shrink Small Outline (ST) - 4.4 mm Body [TSSOP]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging

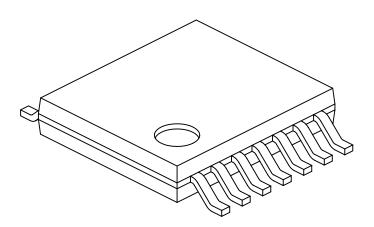




Microchip Technology Drawing C04-087C Sheet 1 of 2

#### 14-Lead Plastic Thin Shrink Small Outline (ST) - 4.4 mm Body [TSSOP]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	MILLIMETERS				
Dimension	Limits	MIN	NOM	MAX	
Number of Pins	N		14		
Pitch	е		0.65 BSC		
Overall Height	A	-	1.2		
Molded Package Thickness	A2	0.80	1.00	1.05	
Standoff	A1	0.05	-	0.15	
Overall Width	E	6.40 BSC			
Molded Package Width	E1	4.30	4.40	4.50	
Molded Package Length	D	4.90	5.00	5.10	
Foot Length	L	0.45	0.60	0.75	
Footprint	(L1)	1.00 REF			
Foot Angle	φ	0°	-	8°	
Lead Thickness	С	0.09	-	0.20	
Lead Width	b	0.19	-	0.30	

Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.

2. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15mm per side.

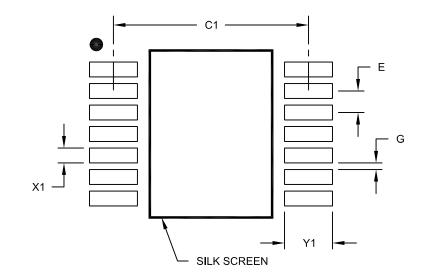
3. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances. REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing No. C04-087C Sheet 2 of 2

#### 14-Lead Plastic Thin Shrink Small Outline (ST) - 4.4 mm Body [TSSOP]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



#### RECOMMENDED LAND PATTERN

	Units		MILLIMETERS			
Dimensi	Dimension Limits		NOM	MAX		
Contact Pitch	E	0.65 BSC				
Contact Pad Spacing	C1		5.90			
Contact Pad Width (X14)	X1			0.45		
Contact Pad Length (X14)	Y1			1.45		
Distance Between Pads	G	0.20				

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2087A

#### APPENDIX A: REVISION HISTORY

#### **Revision D (September 2011)**

The following is the list of modifications:

1. Section 1.0 "Electrical Characteristics": Updated minor typographical corrections in both "DC Electrical Specifications" tables to show the correct unit for  $R_L$  (k $\Omega$  instead of kW).

#### **Revision C (August 2011)**

The following is the list of modifications:

- 1. Added new MCP6406, MCP6407 and MCP6409 devices and the related information throughout the document.
- Created two package type drawings based on the temperature characterization (see E Temp Package Types and H Temp Package Types).
- Added MCP6406/7/9 specification tables in Section 1.3 "MCP6406/7/9 Electrical Specifications".
- 4. Updated characterization graphics in Section 2.0 "Typical Performance Curves".
- 5. Updated **Table 3-1** in **Section 3.0** "**Pin Descriptions**" to show all the devices.
- 6. Updated markings examples in Section 6.1 "Package Marking Information".
- Updated the package markings information to show all drawings available for each type of package.
- 8. Updated the **Product Identification System** page with the new devices and temperature specifications.

#### **Revision B (June 2010)**

The following is the list of modifications:

- 1. Added the MCP6402 and MCP6404 package information.
- 2. Updated the ESD protection value on all pins in Section 1.1 "Absolute Maximum Ratings †".
- 3. Added Figure 2-36.
- 4. Updated Table 3-1.
- 5. Updated Section 4.1.2 "Input Voltage Limits".
- 6. Added Section 4.1.3 "Input Current Limits".
- 7. Added Section 4.5 "Unused Op Amps".
- 8. Updated Section 5.4 "Analog Demonstration and Evaluation Boards".
- 9. Updated the package markings information and drawings.
- 10. Updated the **Product Identification System** page.

#### **Revision A (December 2009)**

Original data sheet for the MCP6401/1R/1U/2/4/6/7/9 family of devices.

#### **PRODUCT IDENTIFICATION SYSTEM**

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.

PART NOX /XX		Exa	Examples:			
•		 :kage	a)	MCP6401T-E/LT:	Tape and Reel, Extended Temperature, 5LD SC70 pkg	
Device:	MCP6401T:	Single Op Amp (Tape and Reel)	b)	MCP6401T-E/OT:	Tape and Reel, Extended Temperature, 5LD SOT-23 pkg	
2011001	MCP6401RT:	(SC70, SOT-23) Single Op Amp (Tape and Reel)	c)	MCP6401RT-E/OT:	Tape and Reel, 5LD SOT-23 pkg	
	MCP6401UT:	(SOT-23) Single Op Amp (Tape and Reel) (SOT-23)	d)	MCP6401UT-E/OT:	Tape and Reel, Extended Temperature, 5LD SOT-23 pkg	
	MCP6402: MCP6402T:	Dual Op Amp Dual Op Amp (Tape and Reel) (SOIC, 2x3 TDFN)	e)	MCP6402-E/SN:	Extended Temperature, 8LD SOIC pkg	
	MCP6404: MCP6404T:	Quad Op Amp Quad Op Amp (Tape and Reel) (SOIC, TSSOP)	f)	MCP6402T-E/SN:	Tape and Reel, Extended Temperature, 8LD SOIC pkg	
	MCP6406T:	Single Op Amp (Tape and Reel) (SOT-23)	g)	MCP6402T-E/MNY:	Tape and Reel, Extended Temperature,	
	MCP6407: MCP6407T:	Dual Op Amp Dual Op Amp (Tape and Reel) (SOIC)	h)	MCP6404-E/SL:	8LD 2x3 TDFN pkg Extended Temperature,	
	MCP6409: MCP6409T:	Quad Op Amp Quad Op Amp (Tape and Reel) (SOIC)	i)	MCP6404T-E/SL:	14LD SOIC pkg Tape and Reel, Extended Temperature, 14LD SOIC pkg	
Temperature Range: E = -40 °C to +125 °C (Exte	to +125 ℃ (Extended Temperature)	j)	MCP6404-E/ST:	Extended Temperature, 14LD TSSOP pkg		
	H = -40°C	to +150℃ (High Temperature)	k)	MCP6404T-E/ST:	Tape and Reel, Extended Temperature, 14LD TSSOP pkg.	
SN = Plastic SOIC, (3.90 mm b MNY* = Plastic Dual Flat, No Lead	c Small Outline Transistor (SOT-23), 5-lead c SOIC, (3.90 mm body), 8-lead c Dual Flat, No Lead, (2x3 TDFN), 8-lead	a)	MCP6401T-H/OT:	Tape and Reel, High Temperature, 5LD SOT-23 pkg		
		c SOIC (3.90 mm body), 14-lead c TSSOP (4.4mm body), 14-lead	b)	MCP6402-H/SN:	High Temperature, 8LD SOIC pkg	
* Y = Nickel palladium gold manufacturing des Only available on the TDFN package.			c)	MCP6402T-H/SN:	Tape and Reel, High Temperature, 8LD SOIC pkg	
			d)	MCP6404-H/SL:	High Temperature, 14LD SOIC pkg	
			e)	MCP6404T-H/SL:	Tape and Reel, High Temperature, 14LD SOIC pkg	
			f)	MCP6406T-H/OT:	Tape and Reel, High Temperature, 5LD SOT-23 pkg	
			g)	MCP6407-H/SN:	High Temperature, 8LD SOIC pkg	
			h)	MCP6407T-H/SN:	Tape and Reel, High Temperature, 8LD SOIC pkg	
			i)	MCP6409-H/SL:	High Temperature, 14LD SOIC pkg	
			j)	MCP6409T-H/SL:	Tape and Reel, High Temperature, 14LD SOIC pkg	

## MCP6401/1R/1U/2/4/6/7/9

NOTES:

#### Note the following details of the code protection feature on Microchip devices:

- · Microchip products meet the specification contained in their particular Microchip Data Sheet.
- Microchip believes that its family of products is one of the most secure families of its kind on the market today, when used in the intended manner and under normal conditions.
- There are dishonest and possibly illegal methods used to breach the code protection feature. All of these methods, to our knowledge, require using the Microchip products in a manner outside the operating specifications contained in Microchip's Data Sheets. Most likely, the person doing so is engaged in theft of intellectual property.
- Microchip is willing to work with the customer who is concerned about the integrity of their code.
- Neither Microchip nor any other semiconductor manufacturer can guarantee the security of their code. Code protection does not mean that we are guaranteeing the product as "unbreakable."

Code protection is constantly evolving. We at Microchip are committed to continuously improving the code protection features of our products. Attempts to break Microchip's code protection feature may be a violation of the Digital Millennium Copyright Act. If such acts allow unauthorized access to your software or other copyrighted work, you may have a right to sue for relief under that Act.

Information contained in this publication regarding device applications and the like is provided only for your convenience and may be superseded by updates. It is your responsibility to ensure that your application meets with your specifications. MICROCHIP MAKES NO REPRESENTATIONS OR WARRANTIES OF ANY KIND WHETHER EXPRESS OR IMPLIED, WRITTEN OR ORAL, STATUTORY OR OTHERWISE, RELATED TO THE INFORMATION, INCLUDING BUT NOT LIMITED TO ITS CONDITION, QUALITY, PERFORMANCE, MERCHANTABILITY OR FITNESS FOR PURPOSE. Microchip disclaims all liability arising from this information and its use. Use of Microchip devices in life support and/or safety applications is entirely at the buyer's risk, and the buyer agrees to defend, indemnify and hold harmless Microchip from any and all damages, claims, suits, or expenses resulting from such use. No licenses are conveyed, implicitly or otherwise, under any Microchip intellectual property rights.

## QUALITY MANAGEMENT SYSTEM CERTIFIED BY DNV ISO/TS 16949:2009

#### Trademarks

The Microchip name and logo, the Microchip logo, dsPIC, KEELOQ, KEELOQ logo, MPLAB, PIC, PICmicro, PICSTART, PIC<sup>32</sup> logo, rfPIC and UNI/O are registered trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

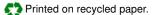
FilterLab, Hampshire, HI-TECH C, Linear Active Thermistor, MXDEV, MXLAB, SEEVAL and The Embedded Control Solutions Company are registered trademarks of Microchip Technology Incorporated in the U.S.A.

Analog-for-the-Digital Age, Application Maestro, chipKIT, chipKIT logo, CodeGuard, dsPICDEM, dsPICDEM.net, dsPICworks, dsSPEAK, ECAN, ECONOMONITOR, FanSense, HI-TIDE, In-Circuit Serial Programming, ICSP, Mindi, MiWi, MPASM, MPLAB Certified logo, MPLIB, MPLINK, mTouch, Omniscient Code Generation, PICC, PICC-18, PICDEM, PICDEM.net, PICkit, PICtail, REAL ICE, rfLAB, Select Mode, Total Endurance, TSHARC, UniWinDriver, WiperLock and ZENA are trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

SQTP is a service mark of Microchip Technology Incorporated in the U.S.A.

All other trademarks mentioned herein are property of their respective companies.

© 2009-2011, Microchip Technology Incorporated, Printed in the U.S.A., All Rights Reserved.



#### ISBN: 978-1-61341-616-7

Microchip received ISO/TS-16949:2009 certification for its worldwide headquarters, design and wafer fabrication facilities in Chandler and Tempe, Arizona; Gresham, Oregon and design centers in California and India. The Company's quality system processes and procedures are for its PIC® MCUs and dsPIC® DSCs, KEELOQ® code hopping devices, Serial EEPROMs, microperipherals, nonvolatile memory and analog products. In addition, Microchip's quality system for the design and manufacture of development systems is ISO 9001:2000 certified.



### **Worldwide Sales and Service**

#### AMERICAS

Corporate Office 2355 West Chandler Blvd. Chandler, AZ 85224-6199 Tel: 480-792-7200 Fax: 480-792-7277 Technical Support: http://www.microchip.com/ support

Web Address: www.microchip.com

Atlanta Duluth, GA Tel: 678-957-9614 Fax: 678-957-1455

Boston Westborough, MA Tel: 774-760-0087 Fax: 774-760-0088

Chicago Itasca, IL Tel: 630-285-0071 Fax: 630-285-0075

**Cleveland** Independence, OH Tel: 216-447-0464 Fax: 216-447-0643

**Dallas** Addison, TX Tel: 972-818-7423 Fax: 972-818-2924

Detroit Farmington Hills, MI Tel: 248-538-2250 Fax: 248-538-2260

Indianapolis Noblesville, IN Tel: 317-773-8323 Fax: 317-773-5453

Los Angeles Mission Viejo, CA Tel: 949-462-9523 Fax: 949-462-9608

Santa Clara Santa Clara, CA Tel: 408-961-6444 Fax: 408-961-6445

Toronto Mississauga, Ontario, Canada Tel: 905-673-0699 Fax: 905-673-6509

#### ASIA/PACIFIC

Asia Pacific Office Suites 3707-14, 37th Floor Tower 6, The Gateway Harbour City, Kowloon Hong Kong Tel: 852-2401-1200 Fax: 852-2401-3431

Australia - Sydney Tel: 61-2-9868-6733 Fax: 61-2-9868-6755

**China - Beijing** Tel: 86-10-8569-7000 Fax: 86-10-8528-2104

**China - Chengdu** Tel: 86-28-8665-5511 Fax: 86-28-8665-7889

**China - Chongqing** Tel: 86-23-8980-9588 Fax: 86-23-8980-9500

**China - Hangzhou** Tel: 86-571-2819-3187 Fax: 86-571-2819-3189

**China - Hong Kong SAR** Tel: 852-2401-1200 Fax: 852-2401-3431

**China - Nanjing** Tel: 86-25-8473-2460 Fax: 86-25-8473-2470

**China - Qingdao** Tel: 86-532-8502-7355 Fax: 86-532-8502-7205

**China - Shanghai** Tel: 86-21-5407-5533 Fax: 86-21-5407-5066

**China - Shenyang** Tel: 86-24-2334-2829 Fax: 86-24-2334-2393

**China - Shenzhen** Tel: 86-755-8203-2660 Fax: 86-755-8203-1760

**China - Wuhan** Tel: 86-27-5980-5300 Fax: 86-27-5980-5118

**China - Xian** Tel: 86-29-8833-7252 Fax: 86-29-8833-7256

**China - Xiamen** Tel: 86-592-2388138 Fax: 86-592-2388130

**China - Zhuhai** Tel: 86-756-3210040 Fax: 86-756-3210049

#### ASIA/PACIFIC

India - Bangalore Tel: 91-80-3090-4444 Fax: 91-80-3090-4123

**India - New Delhi** Tel: 91-11-4160-8631 Fax: 91-11-4160-8632

India - Pune Tel: 91-20-2566-1512 Fax: 91-20-2566-1513

**Japan - Yokohama** Tel: 81-45-471- 6166 Fax: 81-45-471-6122

**Korea - Daegu** Tel: 82-53-744-4301 Fax: 82-53-744-4302

Korea - Seoul Tel: 82-2-554-7200 Fax: 82-2-558-5932 or 82-2-558-5934

**Malaysia - Kuala Lumpur** Tel: 60-3-6201-9857 Fax: 60-3-6201-9859

**Malaysia - Penang** Tel: 60-4-227-8870 Fax: 60-4-227-4068

Philippines - Manila Tel: 63-2-634-9065 Fax: 63-2-634-9069

**Singapore** Tel: 65-6334-8870 Fax: 65-6334-8850

**Taiwan - Hsin Chu** Tel: 886-3-5778-366 Fax: 886-3-5770-955

**Taiwan - Kaohsiung** Tel: 886-7-536-4818 Fax: 886-7-330-9305

**Taiwan - Taipei** Tel: 886-2-2500-6610 Fax: 886-2-2508-0102

**Thailand - Bangkok** Tel: 66-2-694-1351 Fax: 66-2-694-1350

#### EUROPE

Austria - Wels Tel: 43-7242-2244-39 Fax: 43-7242-2244-393 Denmark - Copenhagen Tel: 45-4450-2828 Fax: 45-4485-2829

France - Paris Tel: 33-1-69-53-63-20 Fax: 33-1-69-30-90-79

**Germany - Munich** Tel: 49-89-627-144-0 Fax: 49-89-627-144-44

**Italy - Milan** Tel: 39-0331-742611 Fax: 39-0331-466781

**Netherlands - Drunen** Tel: 31-416-690399 Fax: 31-416-690340

**Spain - Madrid** Tel: 34-91-708-08-90 Fax: 34-91-708-08-91

**UK - Wokingham** Tel: 44-118-921-5869 Fax: 44-118-921-5820

08/02/11